



8NM70A

Power MOSFET

8A, 700V N-CHANNEL POWER MOSFET

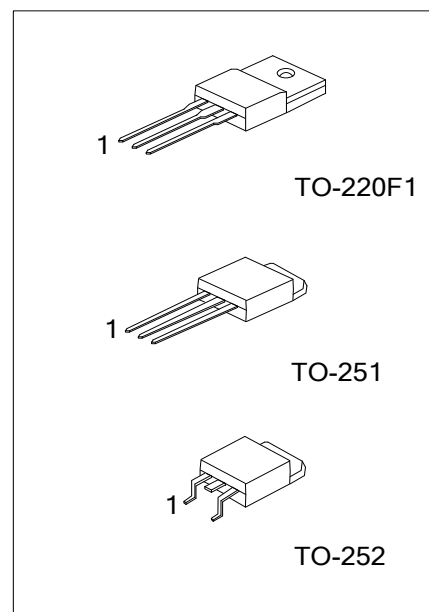
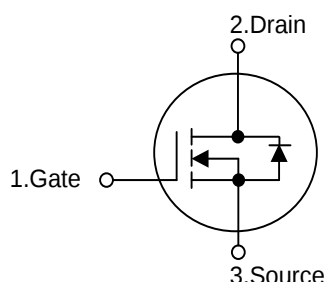
DESCRIPTION

The UTC **8NM70A** is a high voltage super junction MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in switching power supplies and adaptors.

FEATURES

- * $R_{DS(ON)} \leq 0.7 \Omega$ @ $V_{GS}=10V$, $I_D=1.0A$
- * Fast Switching Capability
- * Improved dv/dt Capability, High Ruggedness

SYMBOL



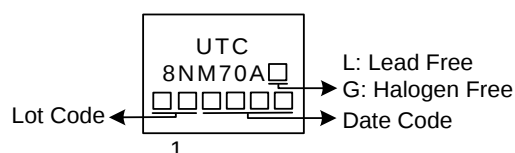
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
8NM70AL-TF1-T	8NM70AG-TF1-T	TO-220F1	G	D	S	Tube
8NM70AL-TM3-T	8NM70AG-TM3-T	TO-251	G	D	S	Tube
8NM70AL-TN3-R	8NM70AG-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

8NM70AG-TF1-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube, R: Tape Reel (2) TF1: TO-220F1, TM3: TO-251, TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free
---	--

MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	8	A
	Pulsed (Note 2)	I_{DM}	32	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	110	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	5.0	V/ns
Power Dissipation	TO-220F1	P_D	28	W
	TO-251/TO-252		54	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=60\text{mH}$, $I_{AS}=1.92\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 8.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220F1	θ_{JA}	62.5	$^\circ\text{C/W}$
	TO-251/TO-252		110	$^\circ\text{C/W}$
Junction to Case	TO-220F1	θ_{JC}	4.46	$^\circ\text{C/W}$
	TO-251/TO-252		2.31 (Note)	$^\circ\text{C/W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

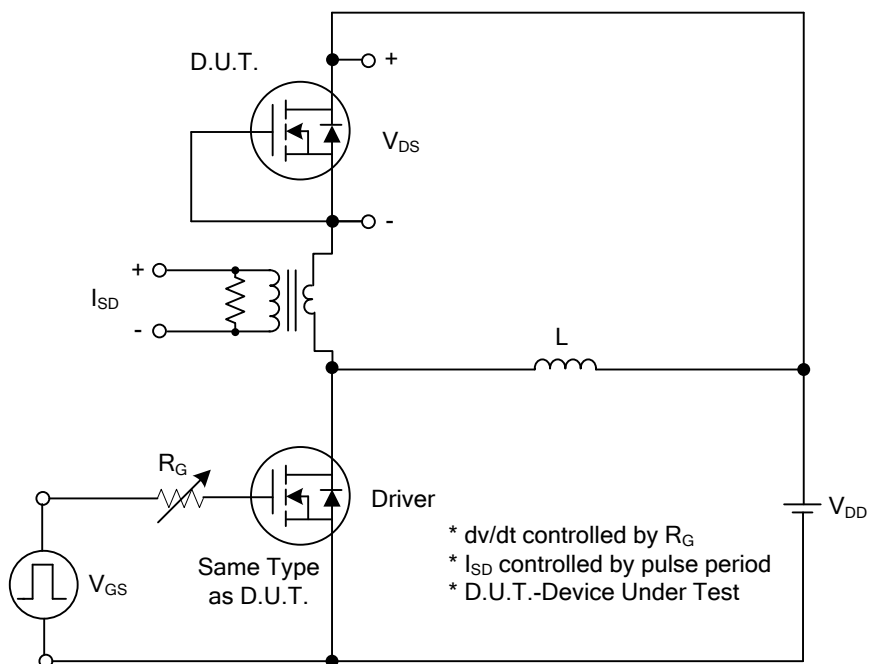
■ **ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0V, I _D = 250μA	700			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 700V, V _{GS} = 0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30V, V _{DS} = 0V			100	nA
	Reverse		V _{GS} = -30V, V _{DS} = 0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} = 10V, I _D = 1.0A			0.7	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0 MHz		451		pF
Output Capacitance		C _{OSS}			260		pF
Reverse Transfer Capacitance		C _{RSS}			25		pF
Gate Resistance		R _G	V _{GS} =0V, f=1.0MHz		2.2		Ω
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A, I _G =100μA (Note 1, 2)		17.8		nC
Gate to Source Charge		Q _{GS}			4.6		nC
Gate to Drain Charge		Q _{GD}			10.4		nC
Turn-on Delay Time (Note 1)		t _{D(ON)}	V _{DD} =30V, V _{GS} =10V, I _D =0.5A, R _G =25Ω (Note 1, 2)		43		ns
Rise Time		t _R			78		ns
Turn-off Delay Time		t _{D(OFF)}			174		ns
Fall-Time		t _F			60		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Pulsed Current		I _S				8	A
Drain-Source Diode Forward Voltage (Note 1)		I _{SM}				32	A
Maximum Body-Diode Continuous Current		V _{SD}	I _S =8.0A, V _{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)		t _{rr}	I _S =8.0A, V _{GS} =0V		328		ns
Reverse Recovery Charge		Q _{rr}	dl _F /dt=100A/μs		3.94		μC

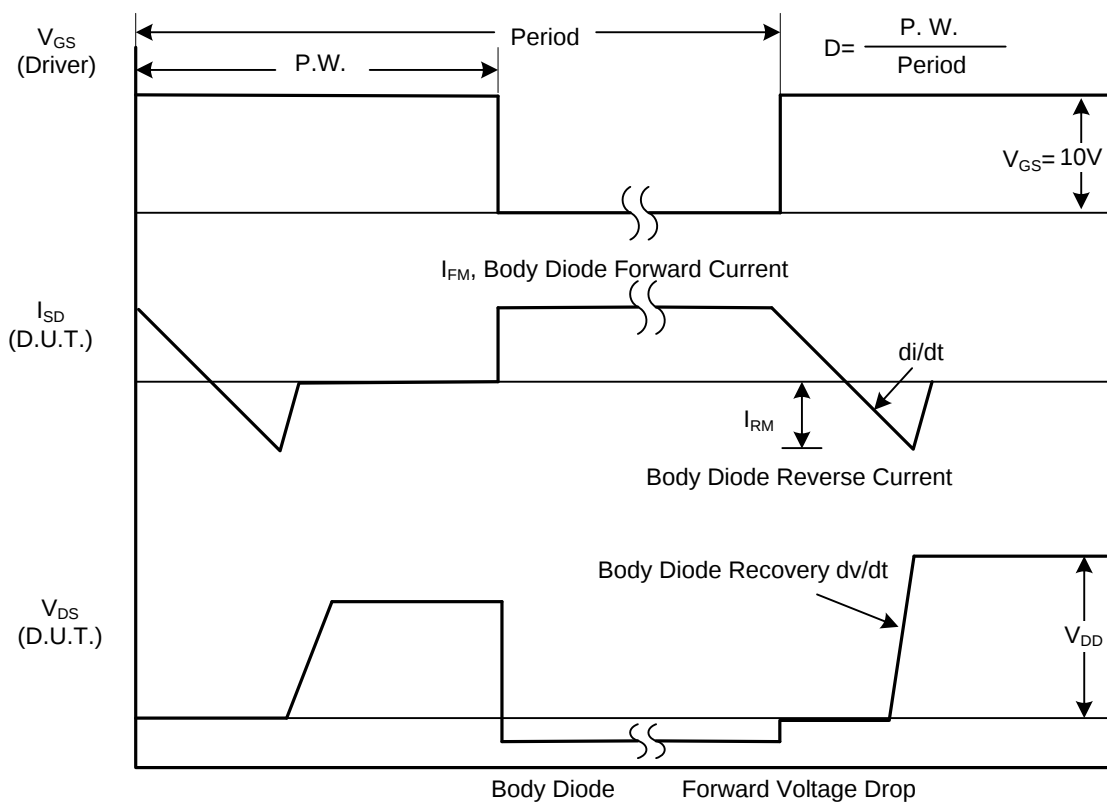
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

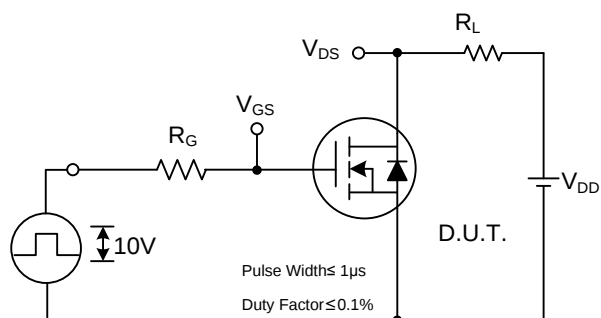


Peak Diode Recovery dv/dt Test Circuit

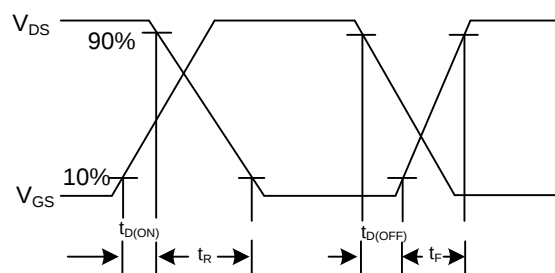


Peak Diode Recovery dv/dt Waveforms

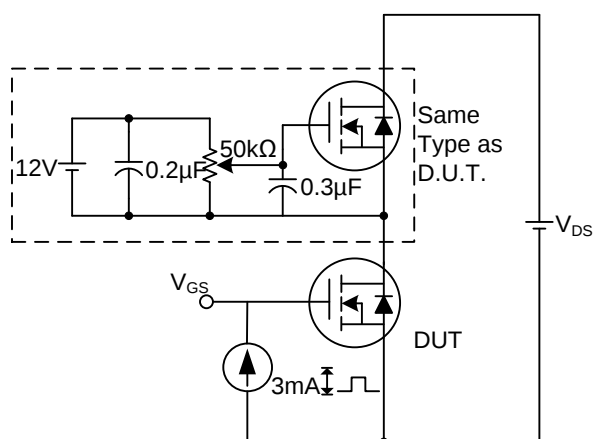
■ TEST CIRCUITS AND WAVEFORMS



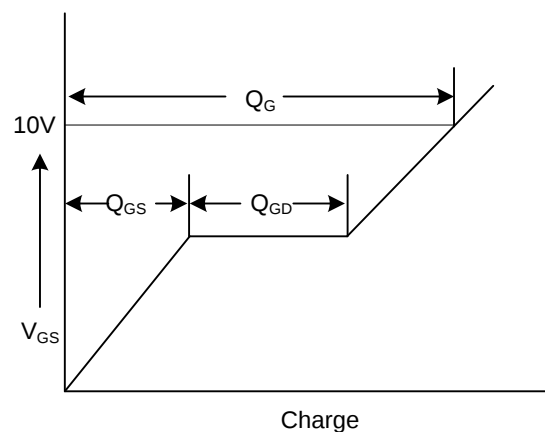
Switching Test Circuit



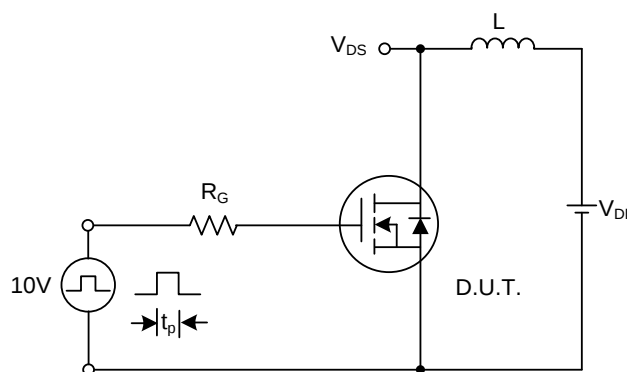
Switching Waveforms



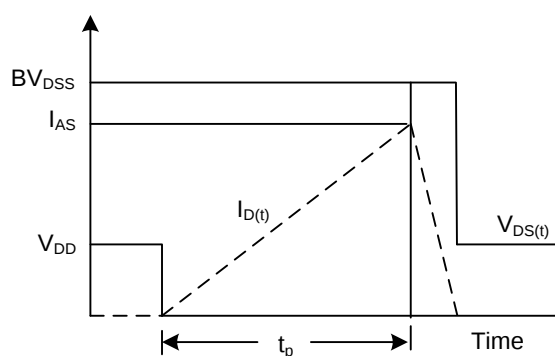
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.